NSN 5961-01-282-8319



Transistor - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5961-01-282-8319 **Inclosure Material:** Metal **Overall Length:** 1.330 inches **Mounting Facility Quantity: Internal Configuration:** Field effect Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-61 isolated **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.570 inches and 0.610 inches **Thread Size:** 0.250 inches **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 200.0 drain to source voltage and 20.0 gate to source voltage **Current Rating Per Characteristic:** 18.00 amperes drain current and 18.00 amperes source current **Power Rating Per Characteristic:** 125.0 watts total device dissipation **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Special Features:** Hardness critical item **Nuclear Hardness Critical Feature:** Hardened **Test Data Document:** 19200-12325158 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:**

Unf

Terminal Type And Quantity:

3 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A110a0